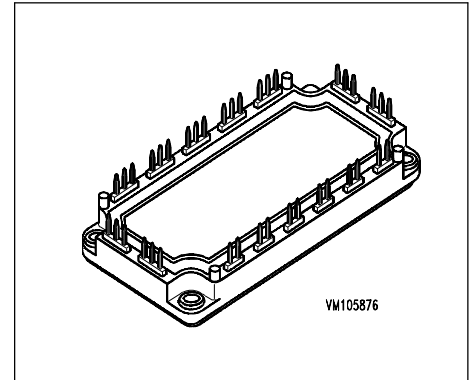


IGBT Power Module

- Solderable Power module
- 3-phase full-bridge
- Including fast free-wheel diodes
- Package with insulated metal base plate



Type	V_{CE}	I_C	Package	Ordering Code
BSM 75 GD 120 DN2	1200V	103A	ECONOPACK 3	C67070-A2516-A67

Maximum Ratings

Parameter	Symbol	Values	Unit
Collector-emitter voltage	V_{CE}	1200	V
Collector-gate voltage	V_{CGR}		
$R_{GE} = 20\text{ k}\Omega$		1200	
Gate-emitter voltage	V_{GE}	± 20	
DC collector current	I_C		A
$T_C = 25\text{ }^{\circ}\text{C}$		103	
$T_C = 80\text{ }^{\circ}\text{C}$		75	
Pulsed collector current, $t_p = 1\text{ ms}$	I_{Cpuls}		
$T_C = 25\text{ }^{\circ}\text{C}$		206	
$T_C = 80\text{ }^{\circ}\text{C}$		150	
Power dissipation per IGBT	P_{tot}		W
$T_C = 25\text{ }^{\circ}\text{C}$		520	
Chip temperature	T_j	+ 150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-40 ... + 125	
Thermal resistance, chip case	R_{thJC}	≤ 0.235	K/W
Diode thermal resistance, chip case	R_{thJCD}	≤ 0.55	
Insulation test voltage, $t = 1\text{min.}$	V_{is}	2500	Vac
Creepage distance	-	16	mm
Clearance	-	11	
DIN humidity category, DIN 40 040	-	F	sec
IEC climatic category, DIN IEC 68-1	-	40 / 125 / 56	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Static Characteristics

Gate threshold voltage $V_{GE} = V_{CE}, I_C = 3\text{ mA}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_j = 125\text{ °C}$	$V_{CE(sat)}$	- -	2.5 3.1	3 3.7	
Zero gate voltage collector current $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$	I_{CES}	- -	1 4	1.5 -	mA
Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	-	-	320	

AC Characteristics

Transconductance $V_{CE} = 20\text{ V}, I_C = 75\text{ A}$	g_{fs}	31	-	-	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{iss}	-	5.1	-	nF
Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{oss}	-	0.72	-	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{rss}	-	0.38	-	

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

Turn-on delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{Gon} = 15\text{ }\Omega$	$t_{d(on)}$	-	30	60	ns
Rise time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 75\text{ A}$ $R_{Gon} = 15\text{ }\Omega$	t_r	-	70	140	
Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 75\text{ A}$ $R_{Goff} = 15\text{ }\Omega$	$t_{d(off)}$	-	450	600	
Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 75\text{ A}$ $R_{Goff} = 15\text{ }\Omega$	t_f	-	70	100	

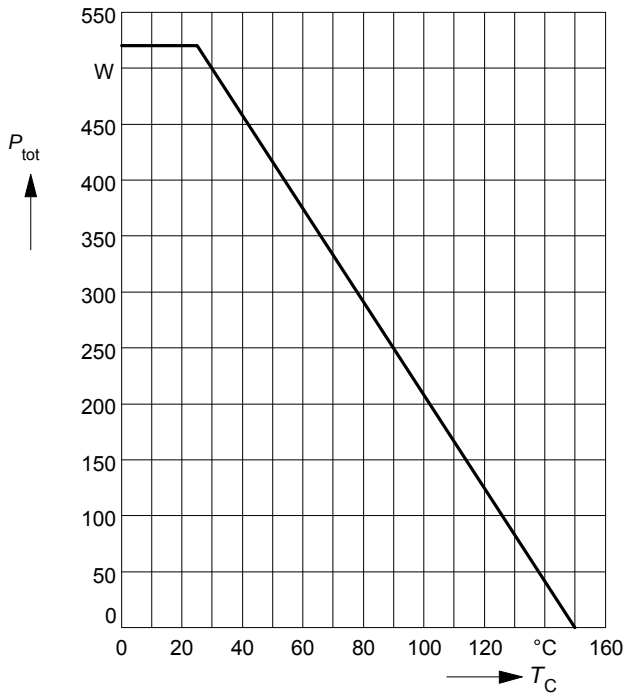
Free-Wheel Diode

Diode forward voltage $I_F = 75\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 75\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$	V_F	-	2.3 1.8	2.8 -	V
Reverse recovery time $I_F = 75\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -900\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$	t_{rr}	-	0.125	-	
Reverse recovery charge $I_F = 75\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -800\text{ A}/\mu\text{s}$, $T_j = 25\text{ °C}$ $di_F/dt = -800\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$ $di_F/dt = -900\text{ A}/\mu\text{s}$, $T_j = 25\text{ °C}$	Q_{rr}	- -	3.2 10	- -	μC

Power dissipation

$$P_{\text{tot}} = f(T_C)$$

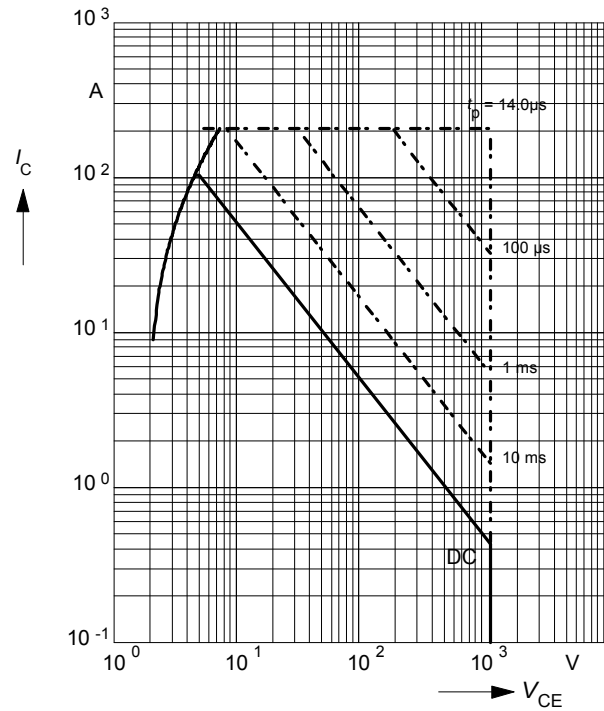
parameter: $T_j \leq 150^\circ\text{C}$



Safe operating area

$$I_C = f(V_{CE})$$

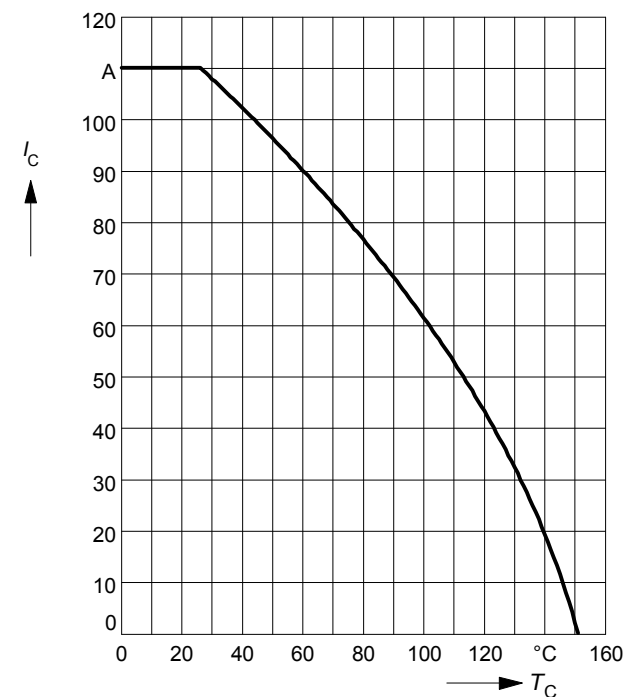
parameter: $D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$



Collector current

$$I_C = f(T_C)$$

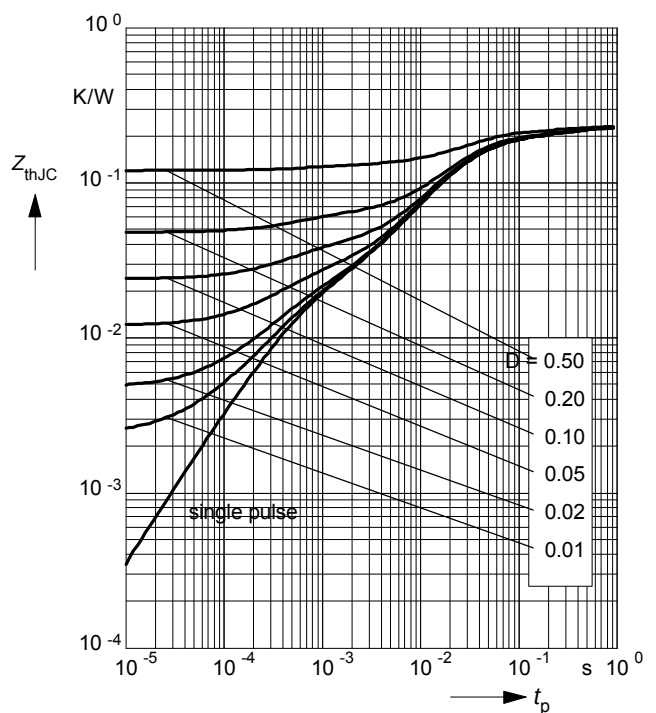
parameter: $V_{GE} \geq 15\text{ V}$, $T_j \leq 150^\circ\text{C}$



Transient thermal impedance IGBT

$$Z_{\text{thJC}} = f(t_p)$$

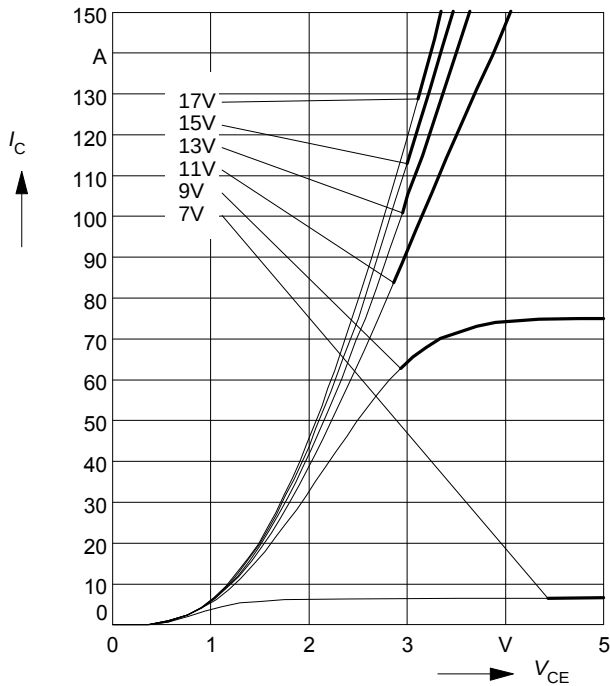
parameter: $D = t_p / T$



Typ. output characteristics

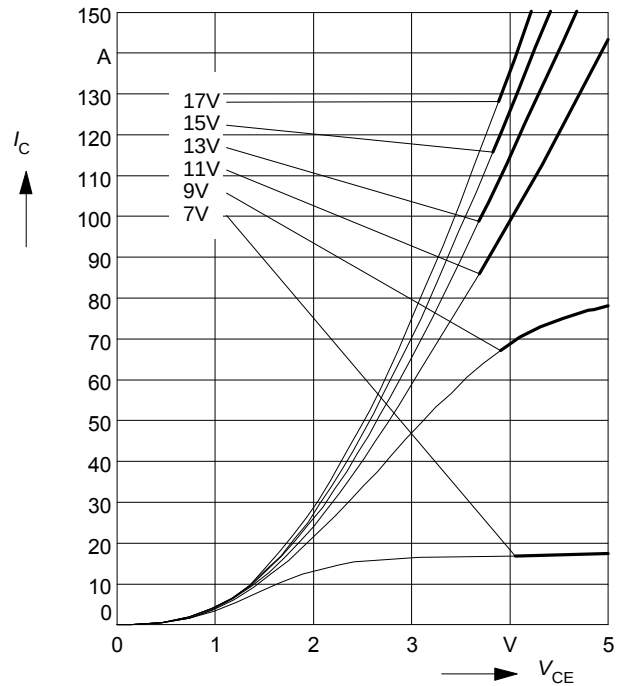
$$I_C = f(V_{CE})$$

parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$

**Typ. output characteristics**

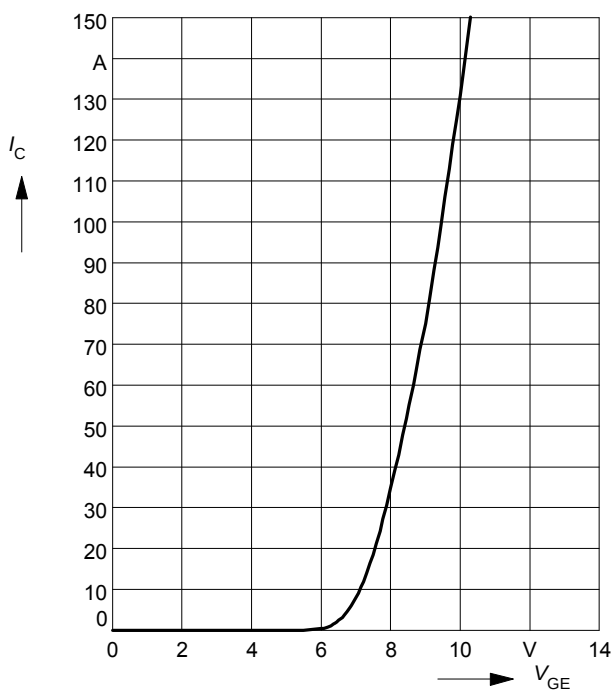
$$I_C = f(V_{CE})$$

parameter: $t_p = 80 \mu s$, $T_j = 125^\circ C$

**Typ. transfer characteristics**

$$I_C = f(V_{GE})$$

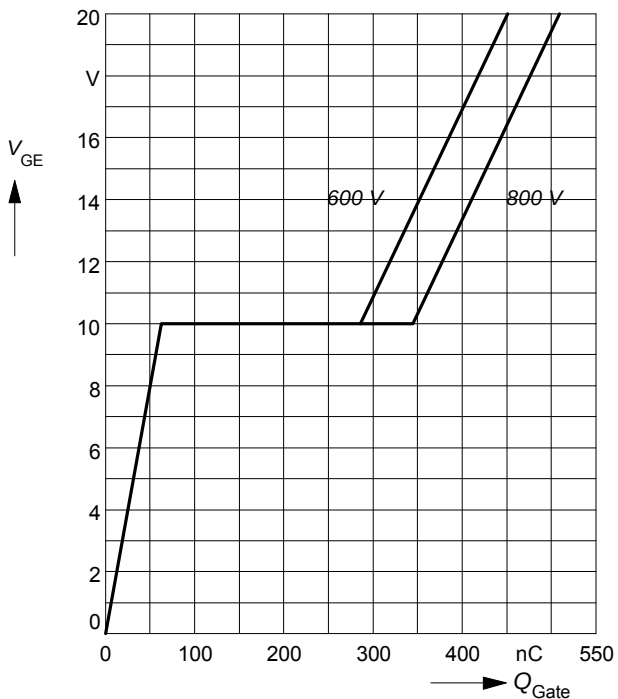
parameter: $t_p = 80 \mu s$, $V_{CE} = 20 V$



Typ. gate charge

$$V_{GE} = f(Q_{Gate})$$

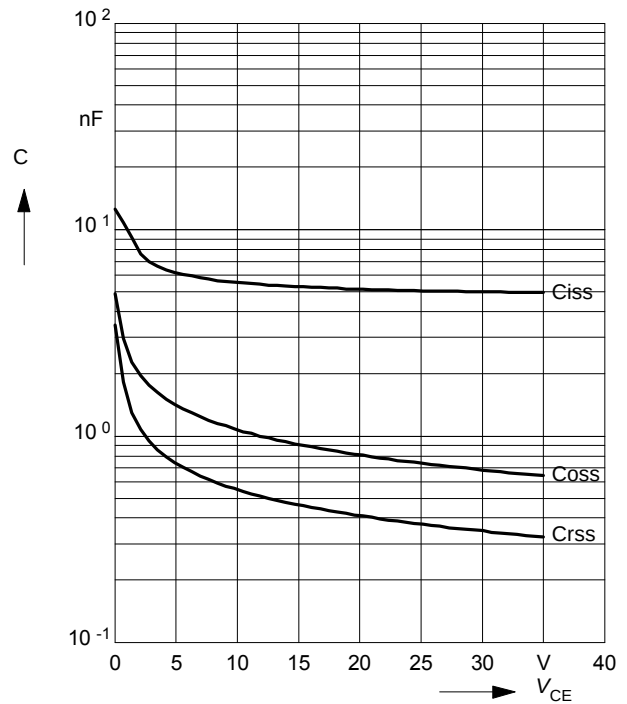
parameter: $I_{C\ puls} = 75\ A$



Typ. capacitances

$$C = f(V_{CE})$$

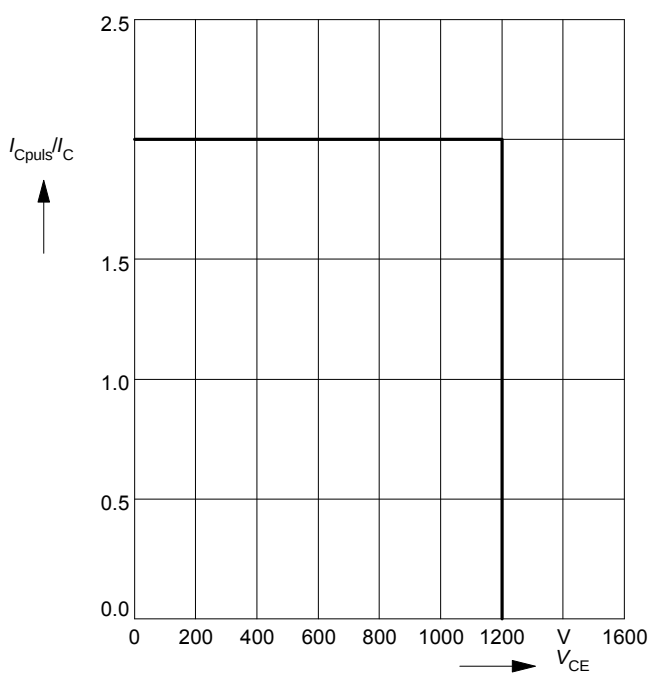
parameter: $V_{GE} = 0\ V$, $f = 1\ MHz$



Reverse biased safe operating area

$$I_{C\ puls} = f(V_{CE}), T_j = 150^\circ C$$

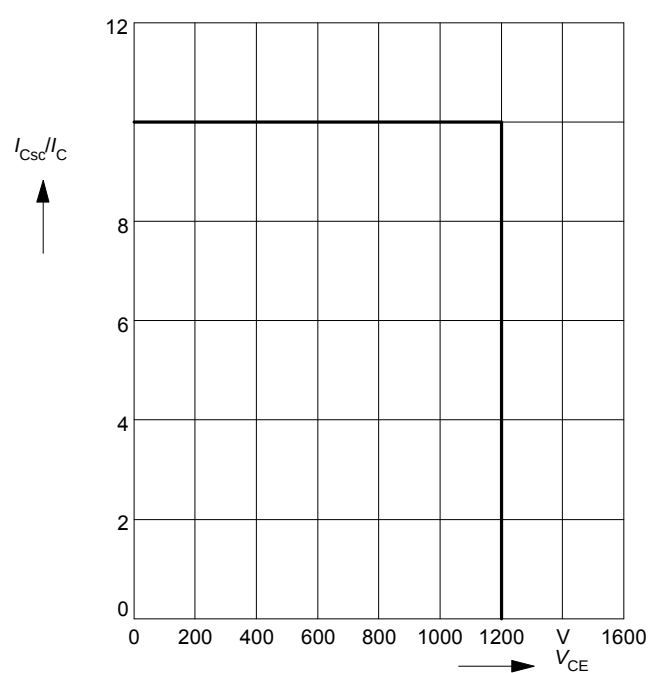
parameter: $V_{GE} = 15\ V$

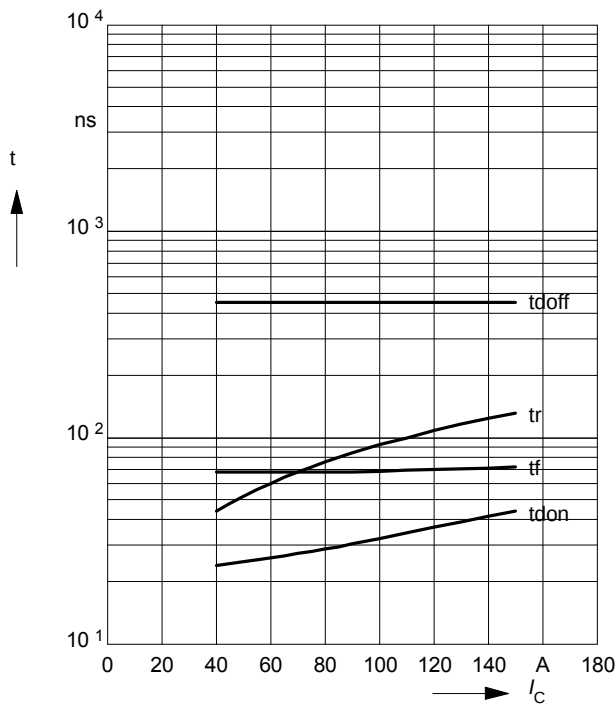
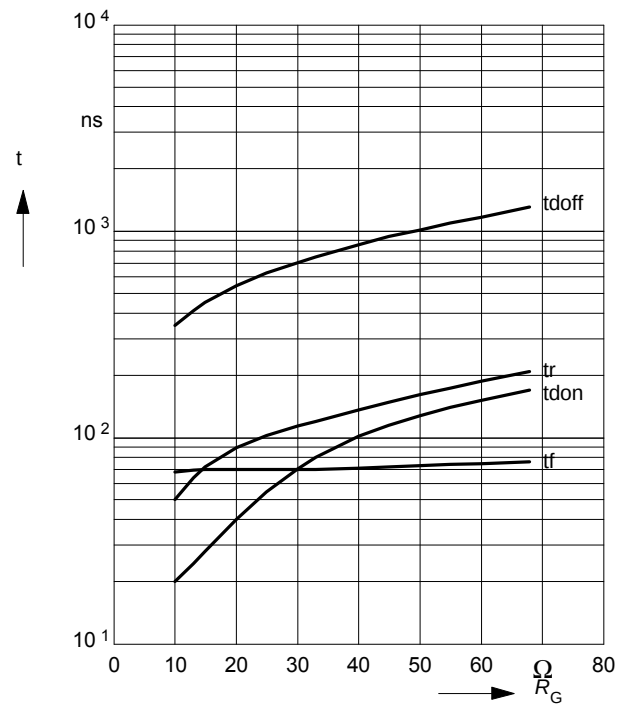
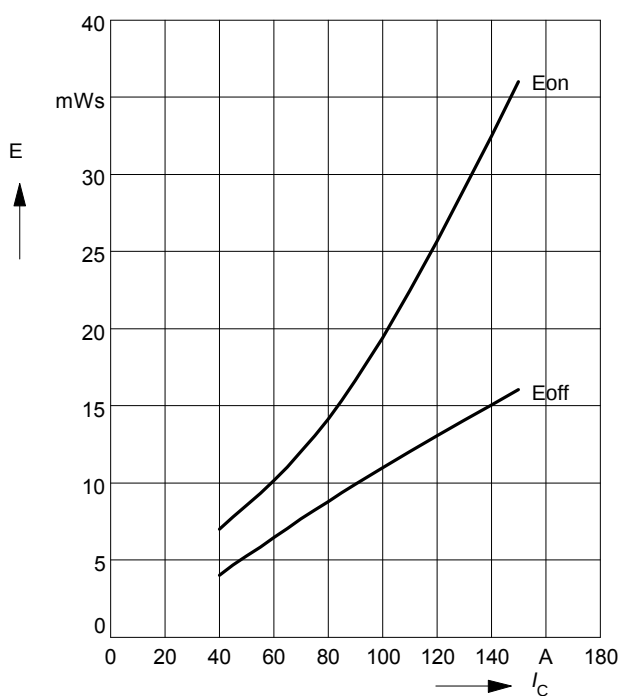
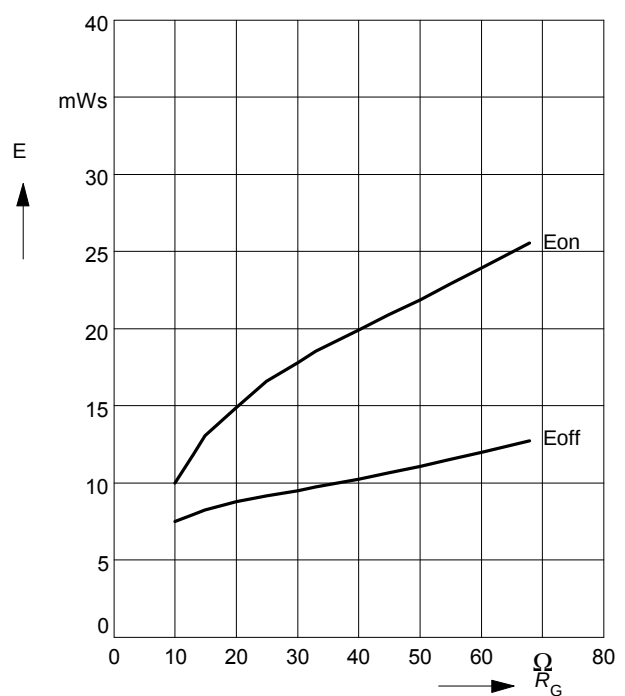


Short circuit safe operating area

$$I_{C\ sc} = f(V_{CE}), T_j = 150^\circ C$$

parameter: $V_{GE} = \pm 15\ V$, $t_{SC} \leq 10\ \mu s$, $L < 50\ nH$

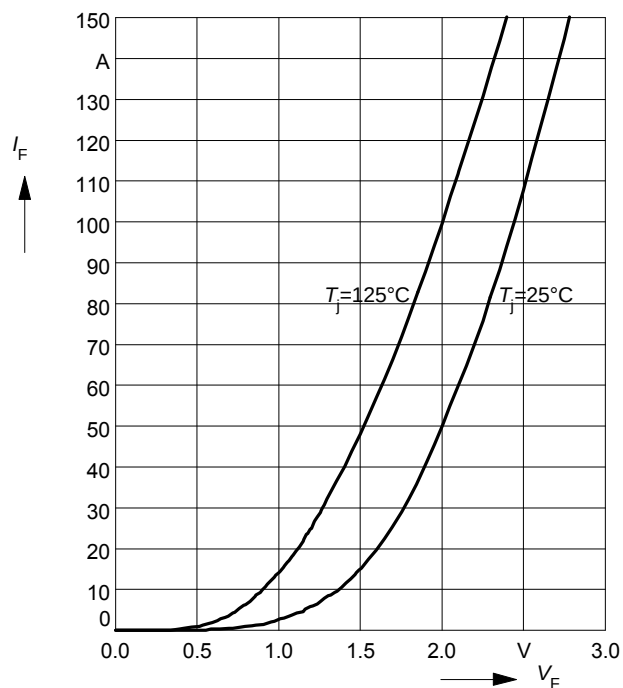


Typ. switching time $I = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 15\ \Omega$ **Typ. switching time** $t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 600\text{ V}$, $I_C = 75\text{ A}$ **Typ. switching losses** $E = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 15\ \Omega$ **Typ. switching losses** $E = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$ par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $I_C = 75\text{ A}$ 

Forward characteristics of fast recovery reverse diode

$I_F = f(V_F)$

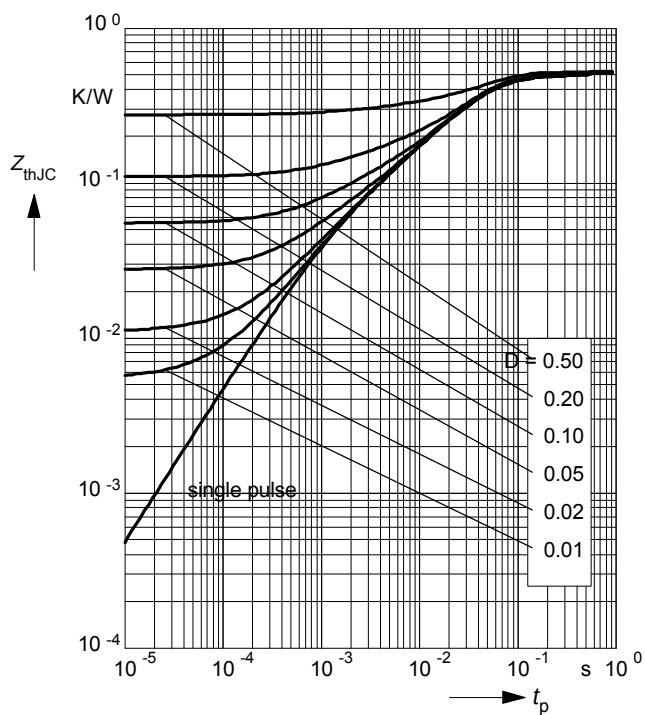
parameter: T_j



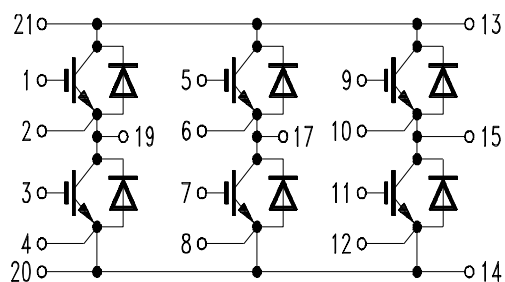
Transient thermal impedance Diode

$Z_{thJC} = f(t_p)$

parameter: $D = t_p / T$



Circuit Diagram



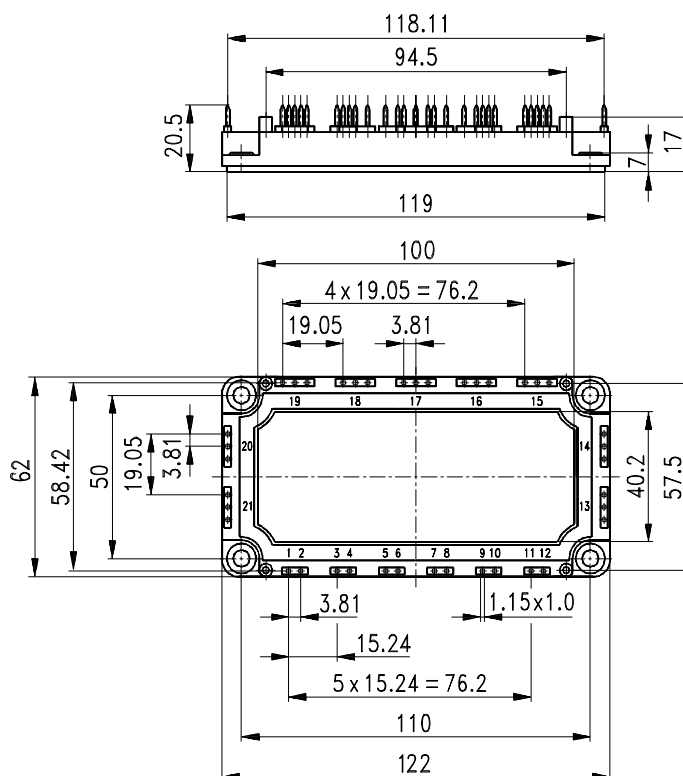
Not connected: 16, 18

SIS00042

Package Outlines

Dimensions in mm

Weight: 300 g



GM105876

Terms & Conditions of Usage

Attention

The present product data is exclusively subscribed to technically experienced staff. This Data Sheet is describing the specification of the products for which a warranty is granted exclusively pursuant the terms and conditions of the supply agreement. There will be no guarantee of any kind for the product and its specifications. Changes to the Data Sheet are reserved.

You and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application. Should you require product information in excess of the data given in the Data Sheet, please contact your local Sales Office via "www.eupec.com / sales & contact".

Warning

Due to technical requirements the products may contain dangerous substances. For information on the types in question please contact your local Sales Office via "www.eupec.com / sales & contact".